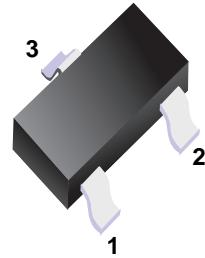


Switching Diodes

■ Features

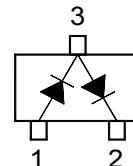
- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance



■ Simplified outline(SOT-523)

■ Marking

Marking	A7
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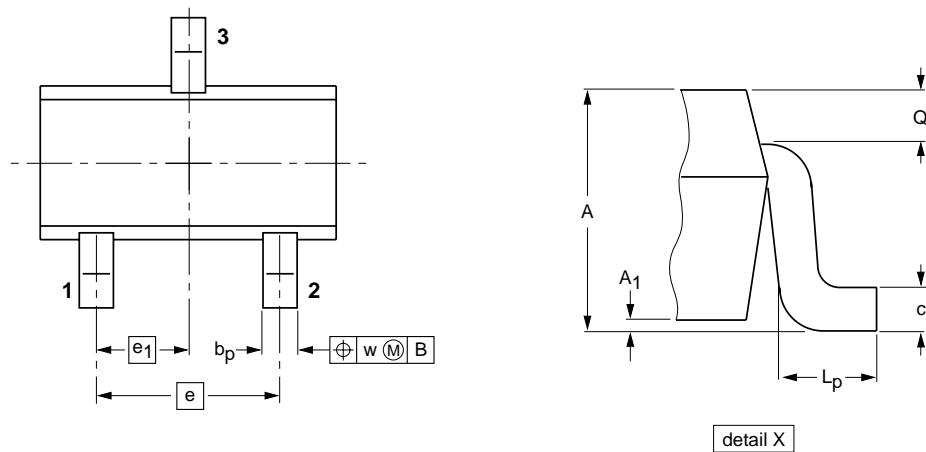
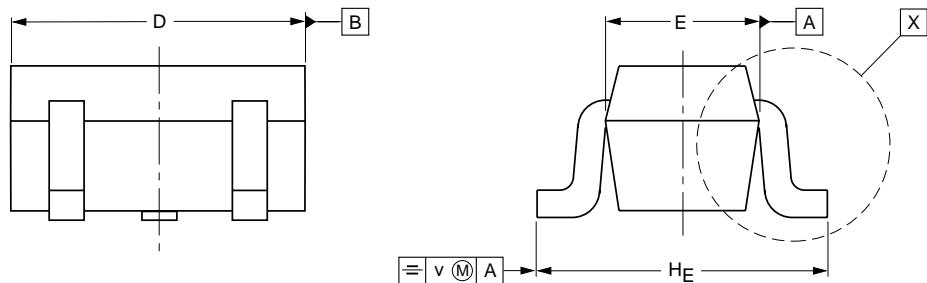
■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current Single Diode Load Double Diode Load	$I_{F(AV)}$	150 130	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current at $t = 1 \mu\text{s}$ at $t = 1 \text{ ms}$ at $t = 1 \text{ s}$	I_{FSM}	4 1 0.5	A
Total Power Dissipation	P_{tot}	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

■ Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Total Capacitance at $V_R = 0, f = 1 \text{ MHz}$	C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$	t_{rr}	4	ns

■ SOT-523



0 0.5 1 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2